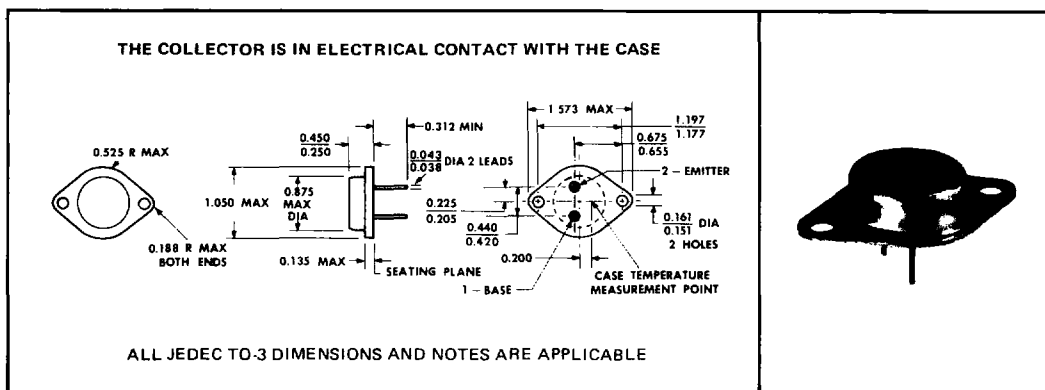


# TYPES 2N3021 THRU 2N3026 P-N-P SILICON POWER TRANSISTORS

FOR POWER-AMPLIFIER AND HIGH-SPEED-SWITCHING APPLICATIONS

- Max  $t_{off}$  400 ns at  $I_C = 1$  A
- 3-A Rated Continuous Collector Current
- 25 Watts at 25°C Case Temperature
- Min  $f_T$  of 60 MHz at 15 V, 0.5 A

\*mechanical data



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\*absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	2N3021	2N3022	2N3023
	2N3024	2N3025	2N3026
Collector-Base Voltage	-30 V	-45 V	-60 V
Collector-Emitter Voltage (See Note 1)	-30 V	-45 V	-60 V
Emitter-Base Voltage	-4 V	-4 V	-4 V
Continuous Collector Current	← -3 A →		
Continuous Base Current	← -0.5 A →		
Safe Operating Areas at (or below) 25°C Case Temperature	See Figures 3 thru 5		
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 2)	← 25 W →		
Operating Collector Junction Temperature Range	-65°C to 175°C		
Storage Temperature Range	-65°C to 175°C		
Terminal Temperature 1/16 Inch from Case for 10 Seconds	← 250°C →		

NOTES: 1. These values apply when the base-emitter diode is open-circuited.  
2. For operation above 25°C case temperature, refer to Dissipation Derating Curve, Figure 6.

\*JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.

# TYPES 2N3021 THRU 2N3026

## P-N-P SILICON POWER TRANSISTORS

\*electrical characteristics of 2N3021, 2N3022, 2N3023 at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N3021		2N3022		2N3023		UNIT	
		MIN	MAX	MIN	MAX	MIN	MAX		
$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage	$I_C = -100 \text{ mA}, I_B = 0$	See Note 3	-30					V	
	$I_C = -50 \text{ mA}, I_B = 0$				-45				
	$I_C = -20 \text{ mA}, I_B = 0$						-60		
$I_{CEV}$ Collector Cutoff Current	$V_{CE} = -25 \text{ V}, V_{BE} = 2 \text{ V}$	-0.2						mA	
	$V_{CE} = -40 \text{ V}, V_{BE} = 2 \text{ V}$			-0.2					
	$V_{CE} = -54 \text{ V}, V_{BE} = 2 \text{ V}$					-0.2			
	$V_{CE} = -15 \text{ V}, V_{BE} = 2 \text{ V}, T_C = 150^\circ\text{C}$	-2							
	$V_{CE} = -25 \text{ V}, V_{BE} = 2 \text{ V}, T_C = 150^\circ\text{C}$			-2					
$I_{EBO}$ Emitter Cutoff Current	$V_{EB} = -4 \text{ V}, I_C = 0$	-1		-1		-1		mA	
$h_{FE}$ Static Forward Current Transfer Ratio	$V_{CE} = -2 \text{ V}, I_C = 1 \text{ A}$	See Notes 3 and 4		20	60	20	60	20	60
$V_{BE}$ Base-Emitter Voltage	$I_C = -3 \text{ A}, I_B = -0.3 \text{ A}$	See Notes 3 and 4		-1.5		-1.5		-1.5	V
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_C = -3 \text{ A}, I_B = -0.3 \text{ A}$	See Notes 3 and 4		-1.5		-1.5		-1.5	V
$ h_{fe} $ Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -15 \text{ V}, I_C = -0.5 \text{ A}, f = 30 \text{ MHz}$	2		2		2			

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\*electrical characteristics of 2N3024, 2N3025, 2N3026 at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N3024		2N3025		2N3026		UNIT	
		MIN	MAX	MIN	MAX	MIN	MAX		
$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage	$I_C = -100 \text{ mA}, I_B = 0$	See Note 3	-30					V	
	$I_C = -50 \text{ mA}, I_B = 0$				-45				
	$I_C = -20 \text{ mA}, I_B = 0$						-60		
$I_{CEV}$ Collector Cutoff Current	$V_{CE} = -25 \text{ V}, V_{BE} = 2 \text{ V}$	-0.2						mA	
	$V_{CE} = -40 \text{ V}, V_{BE} = 2 \text{ V}$			-0.2					
	$V_{CE} = -54 \text{ V}, V_{BE} = 2 \text{ V}$					-0.2			
	$V_{CE} = -15 \text{ V}, V_{BE} = 2 \text{ V}, T_C = 150^\circ\text{C}$	-2							
	$V_{CE} = -25 \text{ V}, V_{BE} = 2 \text{ V}, T_C = 150^\circ\text{C}$			-2					
$I_{EBO}$ Emitter Cutoff Current	$V_{EB} = -4 \text{ V}, I_C = 0$	-1		-1		-1		mA	
$h_{FE}$ Static Forward Current Transfer Ratio	$V_{CE} = -2 \text{ V}, I_C = 1 \text{ A}$	See Notes 3 and 4		50	180	50	180	50	180
$V_{BE}$ Base-Emitter Voltage	$I_C = -3 \text{ A}, I_B = -0.3 \text{ A}$	See Notes 3 and 4		-1.5		-1.5		-1.5	V
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_C = -3 \text{ A}, I_B = -0.3 \text{ A}$	See Notes 3 and 4		-1		-1		-1	V
$ h_{fe} $ Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -15 \text{ V}, I_C = -0.5 \text{ A}, f = 30 \text{ MHz}$	2		2		2			

NOTES: 3. These parameters must be measured using pulse techniques.  $t_w = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 0.125 inch from the device body.

\*JEDEC registered data

# TYPES 2N3021 THRU 2N3026 P-N-P SILICON POWER TRANSISTORS

## \*switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS†		MAX	UNIT
$t_{on}$	Turn-On Time	$I_C = -1$ A, $R_L = 12 \Omega$ .	$I_{B(1)} = -0.1$ A, $V_{BE(off)} = 4$ V, See Figure 1	100	ns
$t_s$	Storage Time	$I_C = -1$ A, $R_L = 12 \Omega$ .	$I_{B(1)} = -0.1$ A, $I_{B(2)} = 0.1$ A, See Figure 2	325	
$t_f$	Fall Time			75	

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

## \*PARAMETER MEASUREMENT INFORMATION

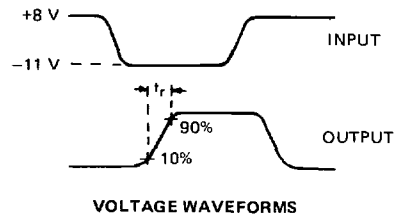
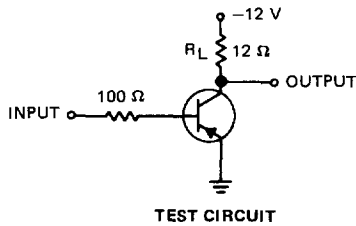


FIGURE 1—RISE TIME

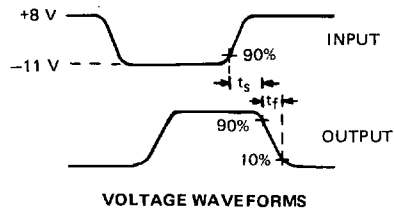
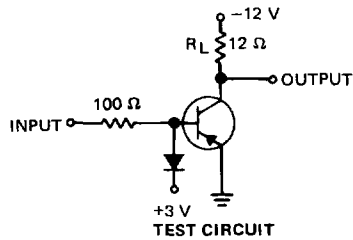


FIGURE 2—STORAGE AND FALL TIMES

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- NOTES: a. The input waveforms are supplied by a generator with the following characteristics:  $t_r \leq 10$  ns,  $t_f \leq 10$  ns,  $t_w = 10$   $\mu$ s,  $Z_{out} = 50 \Omega$ , duty cycle  $\leq 2\%$ .
- b. Waveforms are monitored on an oscilloscope with the following characteristics:  $t_r \leq 5$  ns,  $R_{in} \geq 10$  k $\Omega$ ,  $C_{in} \leq 11.5$  pF.
- c. Resistors must be noninductive types.
- d. The d-c power supplies may require additional bypassing in order to minimize ringing.

\*JEDEC registered data

# TYPES 2N3021 THRU 2N3026

## P-N-P SILICON POWER TRANSISTORS

### MAXIMUM SAFE OPERATING AREAS

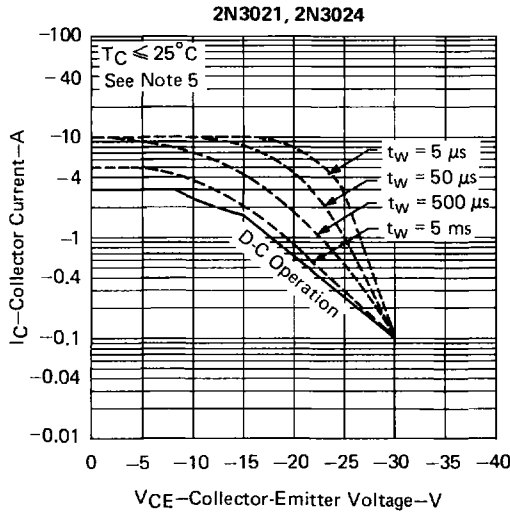


FIGURE 3

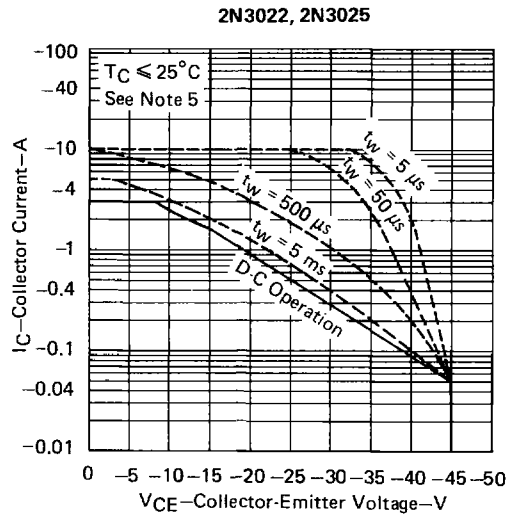


FIGURE 4

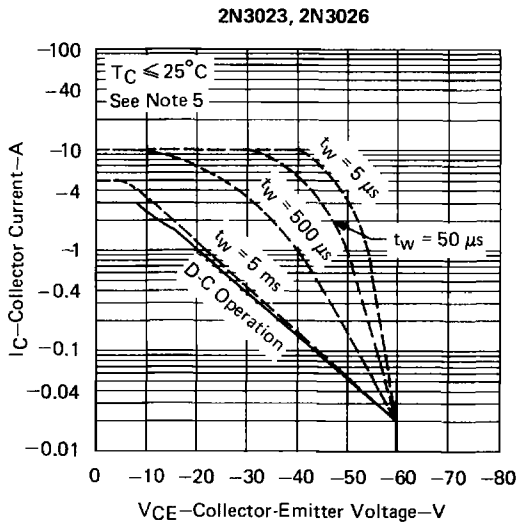


FIGURE 5

NOTE 5: Areas defined by dashed lines apply for nonrepetitive-pulse operation. The pulse may be repeated after the device has regained thermal equilibrium.

### THERMAL INFORMATION

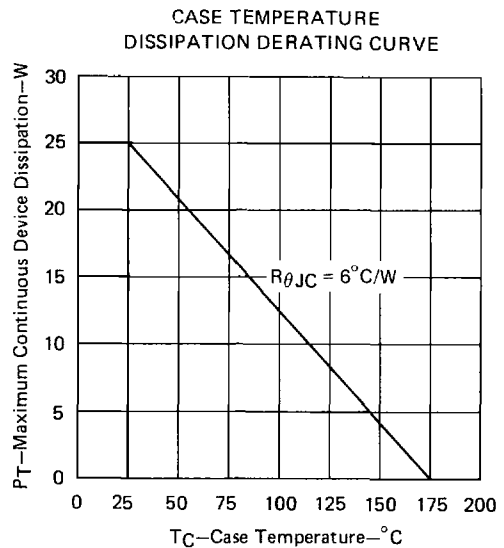


FIGURE 6